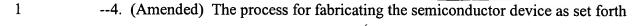
In the Claims:

Please amend claims 1, 4 and 8 in the following manner:

--1. (Amended) A process for fabricating a semiconductor device having a buried layer comprising the steps of: 3 implanting an impurity ion [into] region below a surface of a substrate where [the] a buried layer is to be formed in [a] the substrate; 4 5 [providing] placing the substrate inside a reactor furnace; [preparing] providing a non-oxidizing atmosphere inside of the reactor 6 7 furnace; 8 annealing the substrate to activate and diffuse the implanted impurity ion 9 region while increasing [inside] the internal temperature of the reactor furnace up to a 10 first temperature; and 11 before the ion implanted region beneath the surface of the substrate expands sufficiently to reach the surface of the substrate, changing [shifting] the [inside] 12 13 internal temperature of the reactor furnace from the first temperature to a second 14 temperature [in] at which [a] an epitaxial crystal starts to grow on the surface and 15 introducing [a] an epitaxial growth gas into the reactor furnace to [grow] cause an 16 epitaxial layer to grow on [a] the surface of the substrate.--



² in claim 1 further comprising the steps of:

